Sem in etallic Antiferrom agnetism in the Half-Heusler Structure: CuM nSb

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The halfH eusler compound CuM nSb, the rst antiferrom agnet (AFM) in the M n-based class of H euslers and halfH euslers that contains several conventional and halfm etallic ferrom agnets, shows a peculiar stability of its m agnetic order in high m agnetic elds. D ensity functional based studies reveal an unusual nature of its unstable (and therefore unseen) param agnetic state, which for one electron less (CuM nSn, for example) would be a zero gap sem iconductor (accidentally so) between two sets of very narrow, topologically separate bands of M n 3d character. The extrem ely at M n 3d bands result from the environm ent: M n has four tetrahedrally coordinated Cu atom s whose 3d states lie well below the Ferm i level, and the other four tetrahedrally coordinated sites are empty, leaving chem ically isolated M n 3d states. The AFM phase can be pictured heuristically as a self-doped Cu¹⁺ M n²⁺ Sb³ compensated sem in etal with heavy m ass electrons and light m ass holes, with m agnetic coupling proceeding through K ondo and/or antiK ondo coupling separately through the two carrier types. The ratio of the linear speci c heat coe cient and the calculated Ferm i level density of states indicates a large m ass enhancement m =m 5, or larger if a correlated band structure is taken as the reference.

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I. IN TRODUCTION

The study of unusual magnetic materials has increased dram atically in the past decade, due to new phenom ena such as colossal magnetoresistance, halfmetallic ferromagnetism, spin gaps and novel heavy ferm ion behavior, to name a few. The Heusler (AT₂X type) and half Heusler (ATX type, T = transition metal, X = metal or metalloid) structures have produced a number of unusually interesting compounds. For example, ferrom agnetic (FM) PtM nSb was discovered¹ to display the largest known magneto-optic Kerr e ect at room temperature (at photon energy h! = 1.75 eV). A number of them have been proposed as half metallic ferrom agnets, and N M nSb (with one more electron than CuM nSb) is one of the most widely accepted examples of half metallic ferrom agnetism.

W e address here the half-H eusler com pound C uM nSb, which has its own peculiarities. In a class of interm etallic magnets where ferrom agnetism (FM) can occur as high at 1000 K, CuM nSb develops antiferrom agnetism (AFM) at the relatively low tem perature, with reports of $T_N = 55 \text{ K} \text{ from Endo}_1^2 62 \text{ K} \text{ from Helm holdt et al.}^3$ and 50 K from Boeuf.⁴ A large value of the ordered M n m om ent m = 3.9-4.0 _B has been obtained from neutron scattering m easurem ents.^{3,5} T his m om ent suggests that a \monovalent M n" may provide a good picture, with $d_{\pi}^{5}; d_{\mu}^{1}$ high spin con guration. The Curie-W eiss moment is large, reported variously as 5.4 $_{\rm B}$ [2], 6.3 $_{\rm B}$ [4] and $7.2_{\rm B}$,[6] the latter two of which would be more consistent with a \divalent M n" $d_{\pi}^{5}; d_{\mu}^{0}$ con guration. The Curie-Weiss CW = 160 K suggests large AFM interactions between the M n m om $ents^2$, consistent with the AFM ordering.

CuM nSb is metallic, but experimentally much less so

than the FM compounds in its class. Its D rude plasm a energy was reported 7 as h $_{\rm p}$ = 1.6 eV compared to 2.6–6 eV for the FM Heusler compounds, suggesting a much sm aller density of states and/or Ferm i velocity, and an interband absorption peak was reported at 0.8 eV 8 For a m etal, the square $^2_{\rm p}$ is proportional to N (E $_{\rm F}$)v_{\rm F}^2 (offen interpreted as an elective carrier density to mass ratio (n=m)_{eff}), and this square is a factor or 3–15 lower than its FM counterparts.

The resistivity of CuM nSb shows a fairly rapid drop below T_N , with the samples of Schreiner and Brandao⁹ dropping from around 170 cm above T_N to 50 am at low tem perature. M ore recent work⁴ has low ered these num bers som ew hat: 120 cm above T_N to 45 am at low temperature. Such resistivity drops at magnetic ordering transitions are common and re ect spin scattering that gets frozen out in the ordered phase. In contradiction to this inference, and quite unusual form agnetic com pounds, C uM nSb shows little m agnetoresistance.^{4,6} The still large residual resistivity (45 $(am)^{10}$ in the best sam ples suggests som e intersite disorder or nonstoichiom etry (the em pty site makes half Heuslers susceptible to such defects). Our work indicates this compound to be a sem in etal, however, so this residual resistivity alternatively may re ect primarily a low carrier density for a metal. In both AFM CuM nSb and several FM half Heusler compounds, it has reported that the resistivity is not T² at low tem perature,¹⁰ how ever Boeuf⁴ obtains essentially a T^2 behavior.

Possibly related to some of these features is the fact that C uM nSb displays a curious stability of its magnetic order under applied magnetic elds. The N eel tem perature is invariant for elds up to 14 T.W hereas many AFM s display metam agnetic transitions in a eld, the induced moment at 5 K and H = 12 T is only 0.25 $_{\rm B}$, again re ecting its imperviousness to applied elds. In a more recent work D cerr et al.¹¹ have seen no changes of the antiferrom agnetic characteristics up to 50 T.

The remaining evidence about the electronic state of CuM nSb is from heat capacity (C_V) data.^{4,6} The linear speci cheat coe cient = $17 \,\text{m} \,\text{J/m} \,\text{ol} \,\text{K}^2$ corresponds to a quasiparticle density of states N (E_F) = $7.2 \,\text{states/eV}$ per form ula unit. The T³ coe cient of C_V was reported to be two orders of magnitude larger than the anticipated lattice contribution, which by itself would suggest it is dominated by soft magnetic uctuations. H alfH eusler antim onides have recently attracted attention due to their large therm opower and other prom ising therm oelectric properties,¹² but the Seebeck coe cient of CuM nSb has not been reported.

A lthough there has been alm ost no electronic structure study of C uM nSb, m any other H eusler and half H eusler com pounds have been studied rather thoroughly. A recent analysis of trends in the electronic structure and m agnetization of H eusler com pounds was been presented by G alanakis, D ederichs, and P apanikolaou,¹³ which references much of the earlier work. A recent review concentrating on spintronics applications has been provided by P alm strom .¹⁴ An extensive set of calculations for m any half H eusler com pounds has been presented by N anda and D asgupta.¹⁵ N one of these address C u-containing com pounds, how ever.

In this paper we lay the foundations for an understanding of the electronic properties and m agnetism of C uM nSb by reporting local spin density results for the electronic and m agnetic structures, and the equation of state, for unpolarized, ferrom agnetic, and antiferrom agnetic alignment of the M n spins. The results, such as the AFM ordering and the low density of states at the Ferm i level N (E_F), are in reasonable agreement with experimental data, so it appears that LSDA is accurate for C uM nSb as it is in most other intermetallic 3d com – pounds. The resulting band structure in the AFM phase is rather unusual, being that of a com pensated sem in etal with norm al m ass hole bands but heavy m ass electron bands. Possible correlation e ects are investigated using the correlated band theory (LDA+U) m ethod.

II. STRUCTURE AND METHOD OF CALCULATION

The half Heusler structure is based on the Heusler structural class AT₂X of num erous interm etallic com – pounds, with space group Fm 3m (# 225) whose point group contains all 48 cubic operations. This structure type can be pictured in terms of an underlying bcc arrangement of atom ic sites with lattice constant a/2, with atom A at (0,0,0), X at $(\frac{1}{2};\frac{1}{2};\frac{1}{2})a$, and T at $(\frac{1}{4};\frac{1}{4};\frac{1}{4})a$ and $(\frac{3}{4};\frac{3}{4};\frac{3}{4})a$. Thus the T and X sites lie on the corner sites of the bcc lattice (alternating), while the A sites com prise the body center sites. In the half Heusler structure, one of the T sites is unoccupied. The CuM nSb therefore can

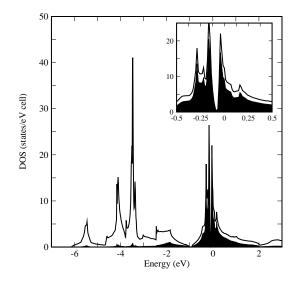


FIG.1: Density of states of nonm agnetic CuM nSb, with the M n 3d contribution shaded. The inset shows the anom alous accidental \zero gap" that occurs slightly below $\rm E_F$.

be viewed as $M nCu_2Sb''$ with the Cu site at $(\frac{1}{2}; \frac{1}{2}; \frac{1}{2})a$ unoccupied.

There are alternative view s of the structure. For example, in AT_2X , the A and X sites form a rocksalt lattice and the T atom s llthe tetrahedral sites of this lattice. A lternatively, in halfH eusler ATX, A and T form a zincblende lattice and half of the interstices (those neighboring T) are lled with X atom s. An alternative view of last choice is the view point of a zincblende lattice form ed of T and X atom s, with A placed at the intersticial site nearest T.W e will study whether any of this view points is preferable to the others.

The half Heusler structure has space group F43m (# 216) with the tetrahedral point group. The crystal structure⁵ is fcc, lattice constant a = 6.088 A, with Mn (A) at (0,0,0), Cu (T) at $(\frac{1}{4};\frac{1}{4};\frac{1}{4})$ and Sb (X) at $(\frac{1}{2};\frac{1}{2};\frac{1}{2})$. The symmetry of all the sites is 43m. It will become signi cant that in this structure the magnetic atom M n is coordinated tetrahedrally by four C u atom s at (3=4)a = 2.64 A, with the other four nearest sites being vacant. M n is second-neighbored by six Sb atom s at a distance of a=2= 3.04 A. The Mn-Cu distance is alm ost identical to the sum of their atom ic radii (1.35 A and 1.28 A, respectively), while the Mn-Sb distance is 3% greater than the sum of their radii (1.35 A and 1.59 A, respectively). The AFM structure consists of alternating (111) planes of Mn atom swith aligned spins. The M n-M n nearest neighbor distance of 4.31 A assures that direct M n-M n exchange is not a dom inant factor in the m agnetic ordering.

Two types of band structure m ethods have been used. The full-potential nonorthogonal local-orbitalm inim um – basis schem e (FPLO)^{16,17} was used for scalar relativistic calculations in the local density approxim ation (LDA) for the exchange-correlation energy¹⁸. Cu 3s; 3p; 4s; 4p; 3d, M n 3s; 3p; 4s; 4p; 3d, and Sb 4s; 4p; 5s; 5p; 4d states were included as valence states. All lower states were treated as core states. We included the relatively extended sem icore 3s; 3p states of C u and M n, and 4s; 4p sem icores of Sb as band states because of the considerable overlap of these states on nearest neighbors. This overlap would be otherwise neglected in the FPLO scheme. The spatial extension of the basis orbitals, controlled by a con ning potential $(r=r_0)^4$, was optimized to minimize the total energy. The self-consistent potentials were calculated on a 12 12 12 k mesh in the Brillouin zone, which corresponds to 116 k points in the irreducible zone.

For the magnetic calculations the full-potential linearized augmented-plane-wave (FLAPW) method as implemented in the Wien2k code¹⁹ was used. The s, p, and d states were treated using the APW + b schem e²⁰, while the standard LAPW expansion was used for higher l's. The basis size was determined by $R_m tK_m ax = 7.0$. The space group of the AFM structure is R3m (#160). The results we present result from use of the Perdew-Burke-E mzerhof generalized gradient approximation form²¹ of exchange-correlation functional, but for the bands and density of states the results are similar to those from the local density approximation.

III. RESULTS OF ELECTRON IC STRUCTURE CALCULATIONS

A. Param agnetic phase

The (unstable) param agnetic electronic structure of C uM nSb is unusual. The density of states (D O S), show n in F ig. 1, exhibits a narrow peak around the Ferm i level $E_{\rm F}$, with an extrem ely narrow valley slightly below $E_{\rm F}$. The ve3d bands that in m etallic M n are spread over 5 eV are here con ned to a 1 eV region centered on $E_{\rm F}$. The split peak is the result of a gap between the disjoint \valence" bands and \conduction" bands, but the gap is indirect and accidentally zero. C uM nSb, with an odd num ber of valence electrons in the primitive cell, cannot be a nonm agnetic insulator, and the occupied states include one electron in what we are referring to as the conduction bands (those above the tiny gap). The upper valence and low er conduction bands show a direct gap of

0.1 eV around the zone edge L, W, and U points. On either side of the gap the bands are at overmost of the surface of the B rillouin zone, and analysis shows that M n t_{2g} character dom inates the bands on both sides of the gap (especially above).

The Heusler and half Heusler structures tend to give rise to such gaps, which is the origin of the various occurrences of half m etallic ferrom agnetism in this structure. One should take the point of view that CuM nSb contains only one transition m etal atom, since the Cu $3d^{10}$ shell is completely led and thus inert. Therefore the Cu 3d states are not involved in a double-peaked complex of narrow bands at E_F . Ironically, we double the cumplet of the cumple

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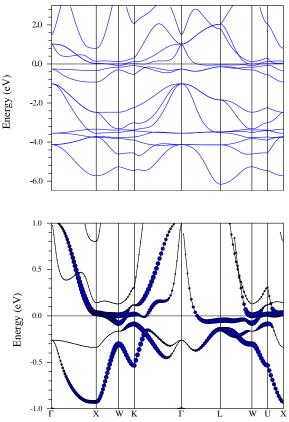


FIG.2: Top panel: nonm agnetic bands of CuM nSb. Notice that the two bands in the -1 eV to E_F region are disjoint from not only the lower bands, but also the near-lying bands above that have the sam e M n 3d character. The indirect gap from K to W is accidentally alm ost zero. Bottom panel: blow up of the bands very near the Ferm i level em phasizing the bands with M n t_{2g} character with larger symbols. Of these ve bands, the ones appearing here as thin lines have e_d character.

of Cu in the compound is the key to the peaked M n 3d DOS and possibly to the peculiarity of the magnetism . The Mn atom sits at the center of a minicube in which it is coordinated tetrahedrally by four Cu atom s, and also tetrahedrally by four unoccupied sites in the half Heusler lattice. Hence the M n 3d states have only the p states of the second neighbor Sb atom s (along the cubic axes) and som e weak C u 4s character to hybridize with and hence to broaden. This coupling is weak, as re ected in the narrow MnDOS.To establish the e ect of Cu quantitatively for states around the Ferm i level, we also carried out a calculation of ⁺¹M nSb, which denotes CuM nSb with the Cu atom removed but leaving its 4s electron (which is simply added to the system). The change is very small near E_F , the one e ect being that the threefold level above E_F at the zone center is shifted upward by 0.6 eV by the presence of Cu.

W hether or not the param agnetic phase has a Stoner instability, it is clear from the huge DOS peaks that a

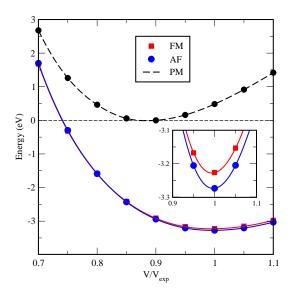


FIG. 3: Calculated equation of state for nonmagnetic (upper curve) and magnetic (lower curves) CuM nSb. On this scale the FM and AFM di erences cannot be distinguished. Note the extrem ely large magnitude of the energy gain from magnetism, and the very large \magnetic expansion" corresponding to almost 4% in the lattice constant.

FM state with nite moment is likely to be energetically favorable to the paramagnetic state. The calculated Ferm i level DOS is N (E_F) = 11.68 states/eV per form ula unit, which corresponds to a linear speci c heat coe cient (without any many body enhancement) of 27.5 m J/m ol-K². A ssum ing the usual value of Stoner interaction parameter I_{M n} 0.75 eV leads to N (E_F)I 9, re ecting a very strong Stoner instability (which occurs anytim e N (E_F)I 1).

B. Ferrom agnetic alignm ent of M n spins

C alculation show sthat either FM or AFM order low ers the energy by more than 3 eV/M n compared to a nonmagnetic conguration, rejecting the energy gain simply from localmoment formation. In addition, there is an energy difference arising from the type of spin alignment. In Fig. 3 the equation of state is pictured for the paramagnetic, FM, and AFM phases. The energy difference between FM and AFM phases is about 50 m eV, a factor of 60 smaller than the energy gain from moment form ation. Hence the Mn moment will be very robust in this compound, independent of degree or type of order. A loo notew orthy is the large difference in volumes, the paramagnetic equilibrium being about 12% smaller in volume (4% smaller lattice constant) than the magnetic phases.

Before moving on to discuss the more stable AFM electronic structure, we analyze brie y the FM results. The exchange splitting of the M n 3d states is 3.5 eV, thus the FM bands look nothing like rigidly shifted replicas of the param agnetic bands, as is evident from the DOS pic-

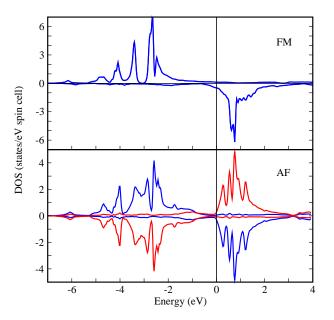


FIG.4: Comparison of the M n partial densities of states for the m agnetic (FM and AFM) con gurations. For FM alignment there is some occupation of of the m inority bands that is evident in the gure. Though less obvious, there is also m inority occupation in the AFM, and the moment is 4 $_{\rm B}$.

tured in Fig. 4. For the unpolarized bands up and down bands are identical and both are about half-lled; after spin polarization, the majority are lled and the minority are nearly empty. The large exchange splitting is characteristic of the large moment, 3.9 $_{\rm B}$ in the M n sphere, 0.1 $_{\rm B}$ from the Cu sphere, and 0.4 $_{\rm B}$ in the interstitial, for a total of 4.4 $_{\rm B}$ per form ula unit. The interstitial contribution is perhaps mostly from M n tails, since the M n majority states are clearly entirely lled (Fig. 4) but there is some small lling of the M n minority 3d states that will reduce the moment somewhat, i.e. 5 (") -0.6 (#) = 4.4 $_{\rm B}$.

Once the moment is formed, the majority Mn 3d bands overlap the Cu 3d bands in energy and mix strongly, and together form two nearly dispersionless complexes of bands along -A at -3.4 eV and -2.75 eV. This repulsive hybridization with the closed 3d shell of Cu should contribute to the large lattice expansion noted above, which is larger than that due to the conventional volum e expansion due to m om ent form ation. The m inority M n 3d states hybridize only with Sb 5p or Cu 4s, and form a narrow set of bands 0.8 eV above E_F that is only 0.4 eV wide (with some tailing). The resulting Ferm i level DOS is quite low, N (E_F) = 0.505 (up) + 0.845 (down) = 1.35 states/eV per form ula unit. W hile this FM alignm ent ism etastable, the EOS calculations show that AFM alignment is more stable, in agreement with experiment. Between the exchange split M n 3d states lie bands with 2-3 eV dispersion that have primarily Sb 5p character.

C. Antiferrom agnetic alignm ent of M n spins

We obtain an AFM state for CuM nSb whose M n 3d density of states is shown in Fig. 4. The magnetic moment lies almost entirely on the M n atom, which is essentially a fully occupied majority and some minority occupation, with moment m = $3.9_{\rm B}$ within the M n sphere of radius 2.2 bohr, in excellent agreement with the measured ordered moment.^{3,5} The M n exchange splitting is $3.5 \, {\rm eV}$, the same as for the FM case and again consistent with the large moment.

Fig. 4 re ects also a very low density of states at $E_{\rm F}$, whose value is N (E $_{\rm F}$) = 1.38 states/eV per form ula unit. As in the param agnetic phase, the valence and conduction bands are disjoint, as can be seen in Fig. 5. There are two sm all, and one larger, Ferm isurface hole cylinders along the -A (0;0; $k_{\rm z}$) line in this gure, which corresponds to one -L < 111 > direction in the original fcc zone. These holes are compensated by electron pockets at the X point of the fcc zone.

D. Possible correlation corrections: LDA + U

It is common for the local spin density approximation to work very well for transition metal intermetallics and in compounds with pnictides, and it has been used extensively in the Heusler and halfHeusler classes. Given the relative chemical isolation of the Mnmoment in CuMnSb, how ever, one may wonder if there are residual correlations elects that should be accounted for, such as with the LDA+U method.²⁵ LDA+U is known to do a good job ofmodeling the band equivalent of the M ott insulator in several systems, mostly oxides. CuMnSb is a metal, and in fact the calculated LSDA DOS seem sto be at least qualitatively reasonable compared to the quasiparticle DOS obtained from the linear speci cheat coel cient. Still, it is important to know if correlation corrections could change the results appreciably.

We have applied the LDA + U functional as adapted to the linearized augmented plane wave method by Shick et al.26 and implemented in the W ien2k code to investigate this question. The LDA+U method requires the values of the M n 3d C oulom b repulsion U and exchange J constants. Because we use the \fully-localized lim it" form²⁷ of functional, we make the common replacement $U ! U_{eff} U J$, and have tried the values U = 2.5, 5.0, and 7.5 eV. The resulting total and Mn-projected DOS are shown in Fig. 6. The occupied and unoccupied M n 3d states behave as expected, each m oving aw ay from the Ferm i level as U is increased. Except for reduction of hybridization due to this shift of 3d states, the bands are changed little. In particular, the band overlap describing a compensated sem in etal rem ains, how ever it is increased by 0.2 eV. The calculated values of N (\mathbb{E}_{F}) for U = 0, 2.5, 5.0, and 7.5 eV are 1.38, 0.76, 0.66, and 0.66states/eV cell (both spins), respectively. Thus the e ect of including U is to reduce the band m ass by as much as

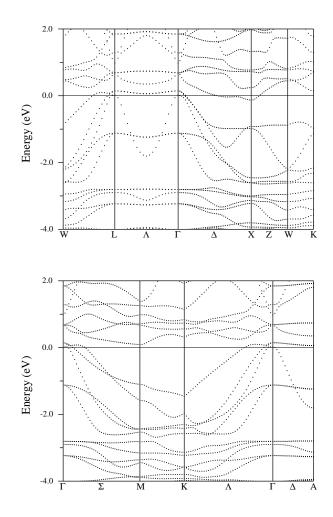


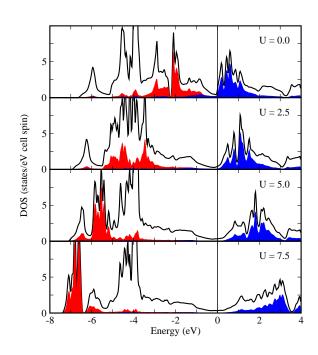
FIG. 5: Bands of antiferrom agnetic CuM nSb, plotted along lines in both the underlying fcc symmetry (top) and in the hexagonal AFM symmetry (bottom). The -L direction shown is along the hexagonal axis of the AFM cell. As for the param agnetic phase, the bands (primarily) below $E_F = 0$ (valence) are disjoint from those above (conduction), but each overlap E_F by 0.1 eV. The exchange split M n 3d bands lie around -3 eV and + 0.5 eV.

50%, due to the reduction of the m inority M n 3d character in the conduction bands. The corresponding values of the M n m om ent (inside the m u n-tin sphere) are 3.87, 4.20, 4.40, 4.52 $_{\rm B}$ respectively.

The band structure for U = 5 eV (which is probably an upper lim it for the value of U for M n in an interm etallic compound) is shown in Fig. 7. The increased band overlap, relative to U = 0, results in larger Ferm i surfaces for both electrons and holes. There is a single electron ellipsoid (at the point that would be X in the cubic Brillouin zone), while there are three closed hole surfaces around both the and A points of the hexagonal Brillouin zone.

The separation (disjointness) between the conduction and valence bands becomes clearer when U > 0 is included (Fig. 7), which rejects some sort of bonding -

Antiferromagnetic CuMnSb: U = 5.0 eV



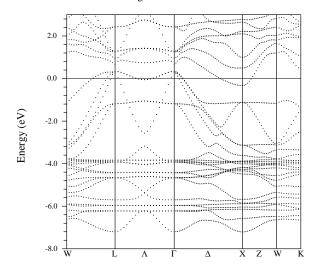


FIG. 6: (color online) Total and M n 3d-projected (lledin regions) density of states of CuM nSb, using the LDA+U m ethod with U = 0 (LDA), 2.5, 5.0, and 7.5 eV (top to bottom). The only noteworthy change is the low ering of occupied, and raising of unoccupied, M n 3d states. The sm all DOS around the Ferm i level rem ains.

antibonding' separation that is not very clear in term s of interaction of atom ic orbitals. One m ight then be concerned about the band gap problem ' in the local density approximation, for which a gap separating bands of distinctly di erent character is usually underestimated. One approximate remedy for this problem is the GW approximation, in which a nonlocal dynamically screened exchange interaction is included.²⁸ The projected density of states how ever show s no clear distinction between the characters of the s p bands below and above the gap, so the self-energy correction is not likely to be large. Since the band structure is that of a heavily doped self-compensated sem iconductor (whether with U = 0 or U = 5 eV), any correction will have some e ect on the carrier density and on the value of N (E_F).

IV. DISCUSSION AND SUMMARY

In this local-density based study of the electronic and m agnetic structure of the half-H eusler m agnet C uM nSb we have found AFM alignment to be energetically favored, consistent with experiment. The moments, for which the LSDA value of 4 $_{\rm B}$ is in excellent agreement with the observed ordered moment, are robust independent of relative orientation. The characters of occupied

FIG.7: Bands of CuM nSb using the LDA + U m ethod, with U = 5 eV, The bands are plotted along the underlying foc lines (compare to the upper panel of Fig. 5) so both electron and hole pockets are evident. The most noticable e ect of including U is the lifting of m inority 3d bands to the ragne 1-3 eV, and alm ost com pletely elim inated 3d character at the Ferm i level.

states indicate that a Cu¹⁺ M n²⁺ Sb³ con guration may be useful starting point for characterizing the electronic structure, although within LSDA there is clearly som e minority 3d occupation. The electronic structures of all phases are representative of narrow M n 3d bands in the midst of much broader bands consisting of Cu 4s, Sb 5s5p, and, further above, M n 4s, and are consistent with earlier calculation of the density of states.²²

The (LSDA) energy di erence of 50 m eV /M n between AFM and FM alignment of spins translates, in a nearest neighbor exchange coupling model, to $J S^2 = 8.3 \text{ m eV}$ which with $S = \frac{5}{2}$ gives J = 1.3 m eV = 15 K. Such a picture of coupling is probably not of quantitative value for C uM nSb, because here interactions between M n spins will be mediated by a low density of sem in etal carriers, leading to coupling with several neighboring shells. There will be two distinct interactions, one through the heavy conduction electrons, another through the light valence band holes. This situation has much in common with $E uB_6$, which a recent study²³ has shown to have two such local-m om ent to itinerant-state interactions, with a di erent sign of the on-site K ondo coupling for valence and conduction bands.

The calculated LDA value of N (E $_{\rm F}$) = 1.38 states/eV per formula unit can be compared with the dressed one obtained from the linear speci c heat coe cient N (E $_{\rm F}$) = 7.2 states/eV per formula unit to obtain a dynamic thermalmass enhancement = m =m -1 4.2.

This result is indicative of a large mass enhancem ent due to spin uctuations. For U = 5 eV, N (E_F) drops to 0.66 states/eV per form ula unit and therm alm ass enhancement increases to 10.

This nonm agnetic electronic structure is rem iniscent of param agnetic FeSi, in which there is a tiny gap²⁴ of 0.13 eV between at bands that are ofm ostly Fe character. In FeSi the Fe m om ent is very obvious in the Curie-W eiss susceptibility at higher tem perature but becom es com pensated at low tem perature and the ground state is param agnetic. In CuM nSb the electron count is such that there is one electron above a sim ilar looking gap. The other clear di erence is that the M n atom rem ains strongly polarized in CuM nSb, while the Fe atom in FeSi loses its m agnetism at low tem perature.

Our study of the electronic structure of CuM nSb reveals that the M n 3d states are virtually chem ically isolated from the environment, leading to very narrow 3d bands and a strong Stoner instability. In the (observed and predicted) antiferrom agnetic state, the system is sem in etallic, with rather norm alm ass Sb 5p hole bands. These bands overlap a single electron band, whose character depends on whether LDA is accurate or if correlations are appreciable. W ithin LDA, the electron band contains som em inority M n 3d character, while this m ixing rapidly disappears if U is appreciable. C om paring the calculated N (E_F) to the speci c heat indicates a m ass enhanœm ent m =m 5 (LDA) or as much as m = m 5 eV). The observed tem perature dependence 11 (U of the transport coe cients show no evidence of heavy

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ferm ion behavior, how ever.

In the transition m etal based H eusler and halfH eusler com pounds ferrom agnetism is common; C uM nSb is practically the only antiferrom agnet. O ur calculations indeed predict that AFM has the lower energy, although exploring the spin coupling m echanisms has not been the purpose of this work. The m agnetic interactions presum ably are m ediated separately through the hole and electron bands, indeed it could be the case that the two m echanisms compete, as has been uncovered recently²³ for EuB₆.

The role of the Cu atom is as a spacer and donor of an electron. Cu is nevertheless crucial, since without it M nSb crystallizes in the hexagonal N iAs structure and is ferrom agnetic rather than antiferrom agnetic. E lectronic structure studies of the N iAs-structure phase as well as the possible zincblende phase have been reported previously.²⁹

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